

VOLTAGE RANGE: 20 - 100V
CURRENT: 1.0 A

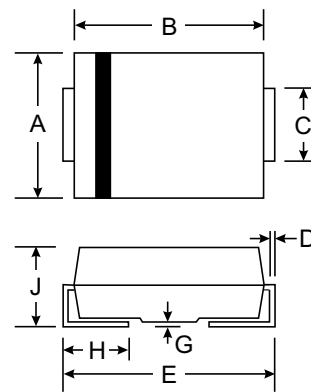
Features

- Schottky Barrier Chip
- Ideally Suited for Automatic Assembly
- Low Power Loss, High Efficiency
- For Use in Low Voltage Application
- Guard Ring Die Construction
- Plastic Case Material has UL Flammability Classification Rating 94V-O



Mechanical Data

- Case: SMA/DO-214AC, Molded Plastic
- Terminals: Solder Plated, Solderable per MIL-STD-750, Method 2026
- Polarity: Cathode Band or Cathode Notch
- Marking: Type Number
- Weight: 0.064 grams (approx.)



SMA(DO-214AC)		
Dim	Min	Max
A	2.29	2.92
B	4.00	4.60
C	1.27	1.63
D	0.15	0.31
E	4.80	5.59
G	0.10	0.20
H	0.76	1.52
J	2.01	2.62
All Dimensions in mm		

Maximum Ratings and Electrical Characteristics T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	SS12	SS13	SS14	SS15	SS16	SS18	SS110	Unit	
Maximum repetitive peak reverse voltage	V _{RRM}	20	30	40	50	60	80	100	V	
Maximum RMS voltage	V _{RMS}	14	21	28	35	42	56	70	V	
Maximum DC blocking voltage	V _{DC}	20	30	40	50	60	80	100	V	
Maximum average forward rectified current at T _L (see fig.1)	I _(AV)	1.0							A	
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	40.0							A	
Maximum instantaneous forward voltage at 1.0A	V _F	0.45	0.55	0.70		0.85			V	
Maximum DC reverse current at rated DC blocking voltage <small>T_A=25°C</small> <small>T_A=100°C</small>	I _R	0.5			5.0				mA	
Typical junction capacitance (NOTE 1)	C _J	110			90				pF	
Typical thermal resistance (NOTE 2)		88.0							°C/W	
Operating junction temperature range	T _J	-65 to +125			-65 to +150					°C
Storage temperature range	T _{STG}	-65 to +150							°C	

Note:

1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
2. P.C.B. mounted with 0.2x0.2" (5.0x5.0mm) copper pad areas

RATINGS AND CHARACTERISTIC CURVES SS12 THRU SS110

